

# **EXHIBIT 15**

**U.S. Patent No. 6,781,858**

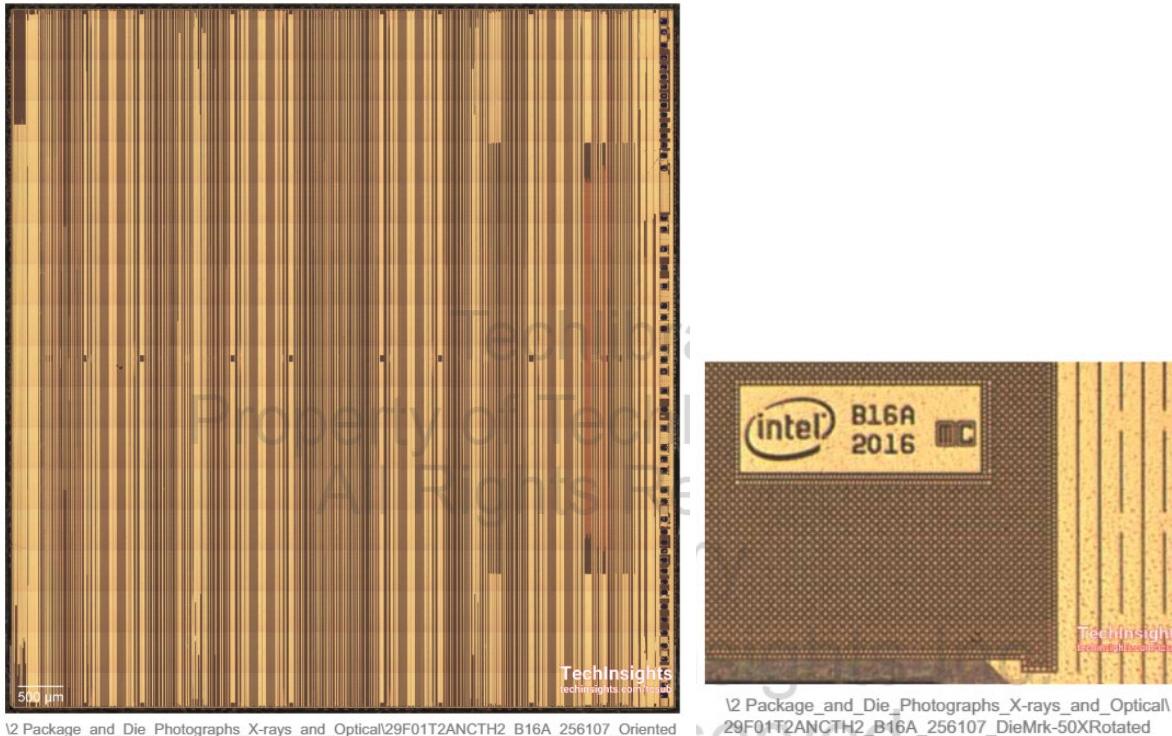
Claim 21	Identification: Lenovo Moto G Power mobile phone <sup>1</sup>										
21. A cubic memory array, comprising:	 A photograph of the Lenovo Moto G Power smartphone standing upright next to its black back cover. The phone's screen displays a colorful home screen with various app icons.	<p><b>moto g</b> <b>POWER</b></p> <p>Go up to three days<sup>t</sup> on a single charge thanks to a 5000 mAh battery.</p> <p>16MP triple camera system. Capture ultra-wide angle panoramas, sharper portraits, and super detailed close-up shots.</p> <p>Dual Stereo Speakers tuned by Dolby®.</p> <table><tbody><tr><td><b>Operating system</b> Android™ 10</td><td><b>Internal storage</b> 64GB built-in<sup>"</sup></td><td><b>Sensors</b> Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)</td></tr><tr><td><b>Processor</b> Qualcomm® Snapdragon™ 665 Mobile Processor</td><td><b>Expandable Storage</b> up to 512GB microSD card expandable<sup>**</sup></td><td><b>Memory (RAM)</b> 4GB</td></tr><tr><td><b>Security</b> Rear fingerprint reader</td><td></td><td></td></tr></tbody></table>	<b>Operating system</b> Android™ 10	<b>Internal storage</b> 64GB built-in <sup>"</sup>	<b>Sensors</b> Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)	<b>Processor</b> Qualcomm® Snapdragon™ 665 Mobile Processor	<b>Expandable Storage</b> up to 512GB microSD card expandable <sup>**</sup>	<b>Memory (RAM)</b> 4GB	<b>Security</b> Rear fingerprint reader		
<b>Operating system</b> Android™ 10	<b>Internal storage</b> 64GB built-in <sup>"</sup>	<b>Sensors</b> Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)									
<b>Processor</b> Qualcomm® Snapdragon™ 665 Mobile Processor	<b>Expandable Storage</b> up to 512GB microSD card expandable <sup>**</sup>	<b>Memory (RAM)</b> 4GB									
<b>Security</b> Rear fingerprint reader											

<https://www.motorola.ca/smartphones-moto-g-power/p?skuId=13>  
[https://www.gsmarena.com/motorola\\_moto\\_g\\_power-10076.php](https://www.gsmarena.com/motorola_moto_g_power-10076.php)

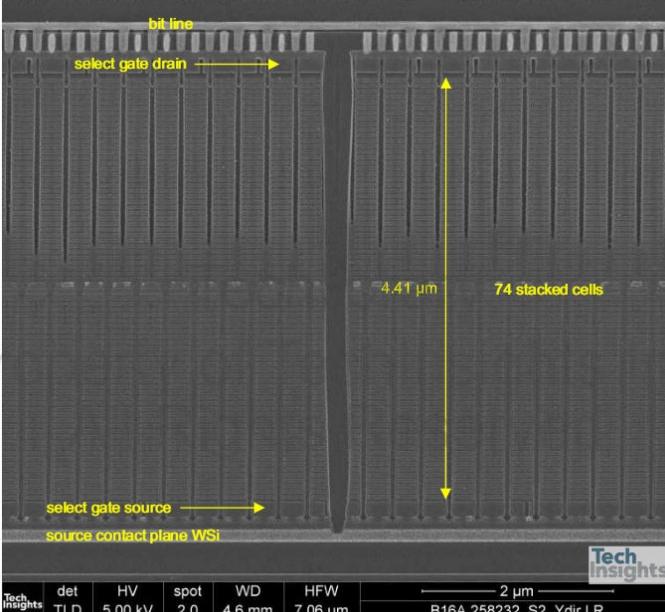
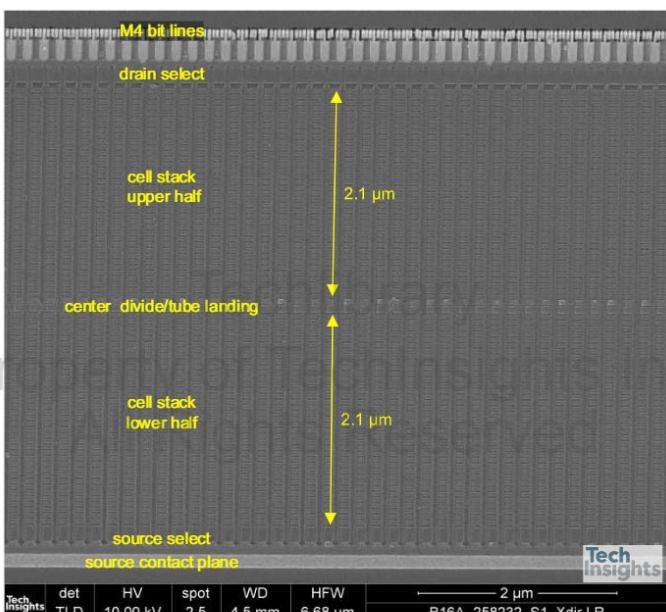
<sup>1</sup> Additional infringing Lenovo devices sold or offered for sale by AT&T, including at least Motorola G Pure, Moto G Play, Moto G7 Play, Moto G Fast devices.

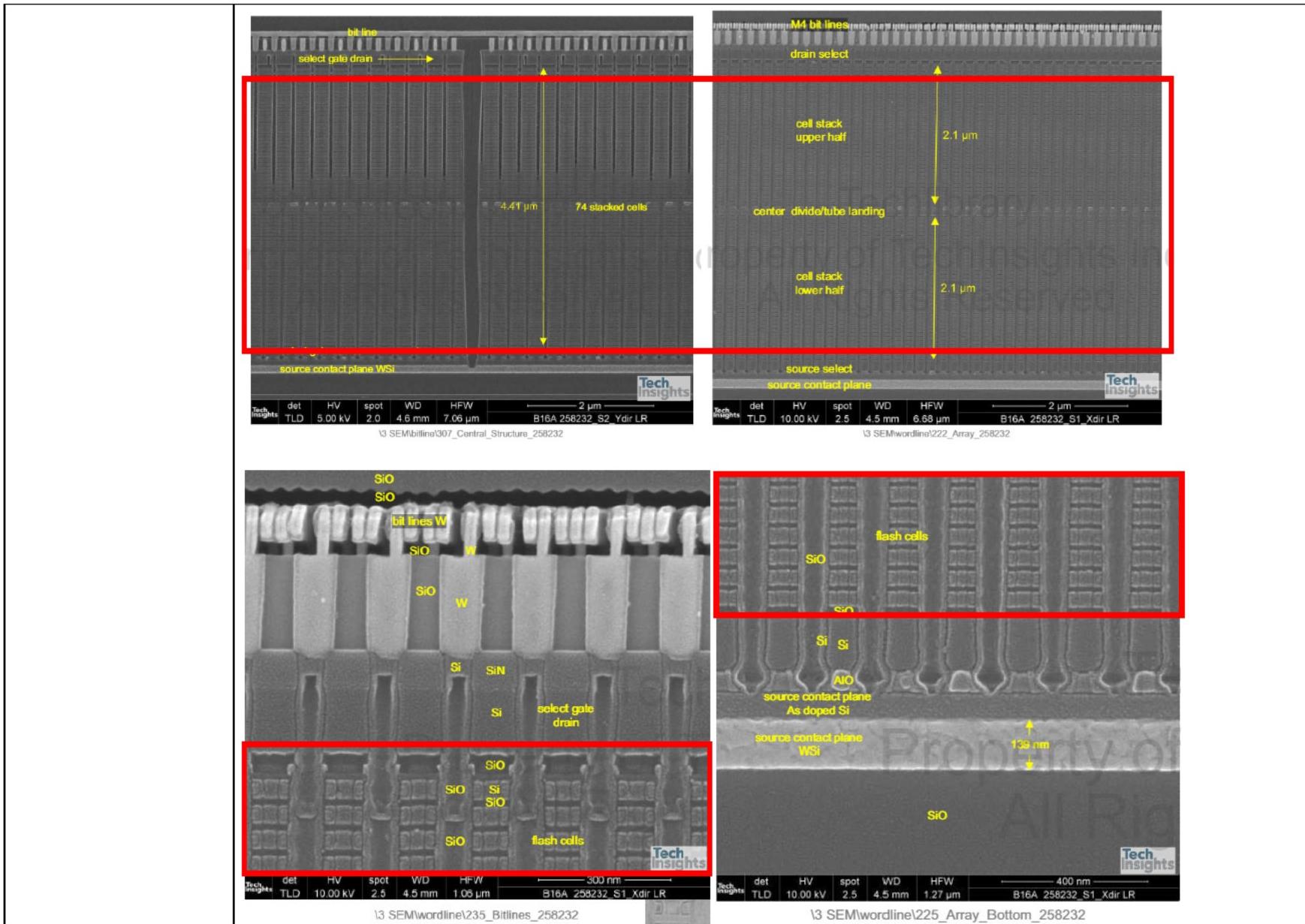
On information and belief, Lenovo Moto G Power mobile phones contain a Micron MT29VZZAD8QKSL-046 multi-chip module with LPDDR4 SDRAM (Z11N die), 3D NAND Flash (B16A die), and eMMC controller (PS8226 die).

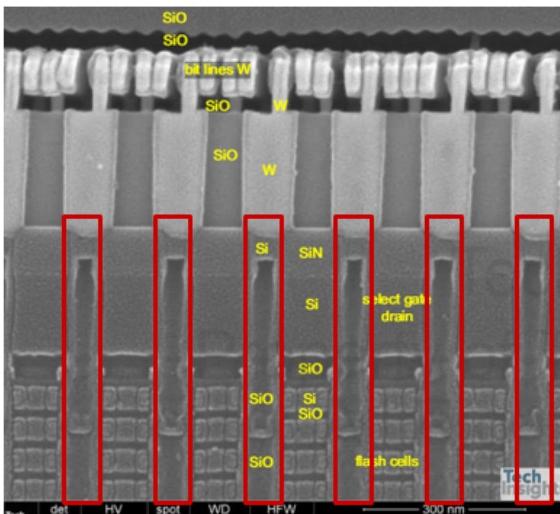
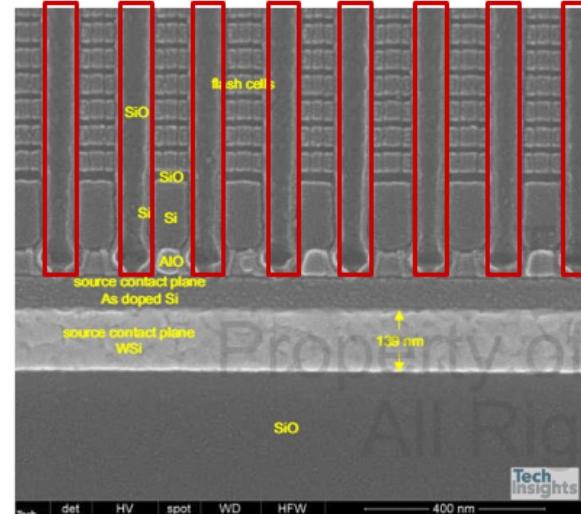
A 3D NAND flash array is a cubic memory array.

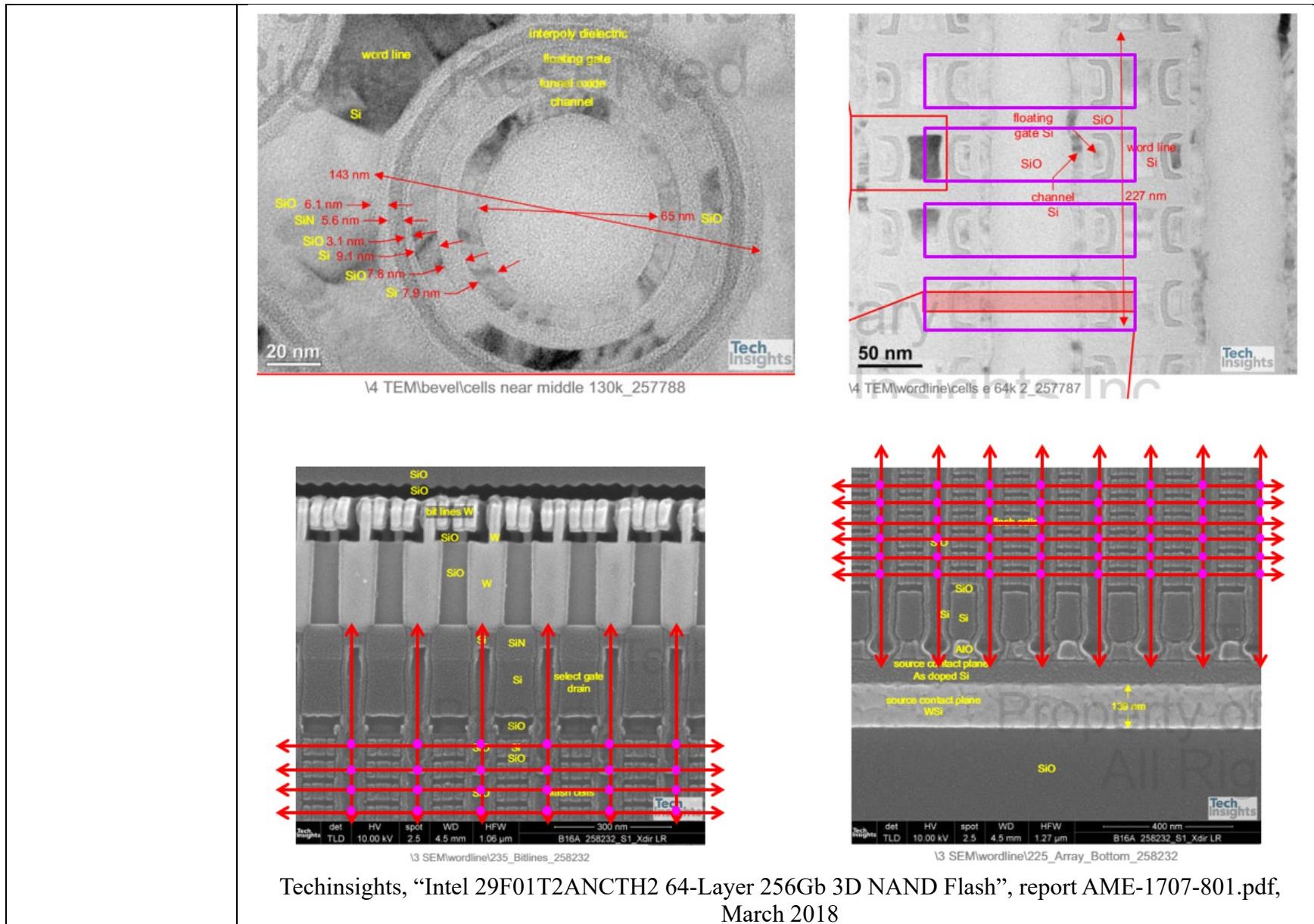


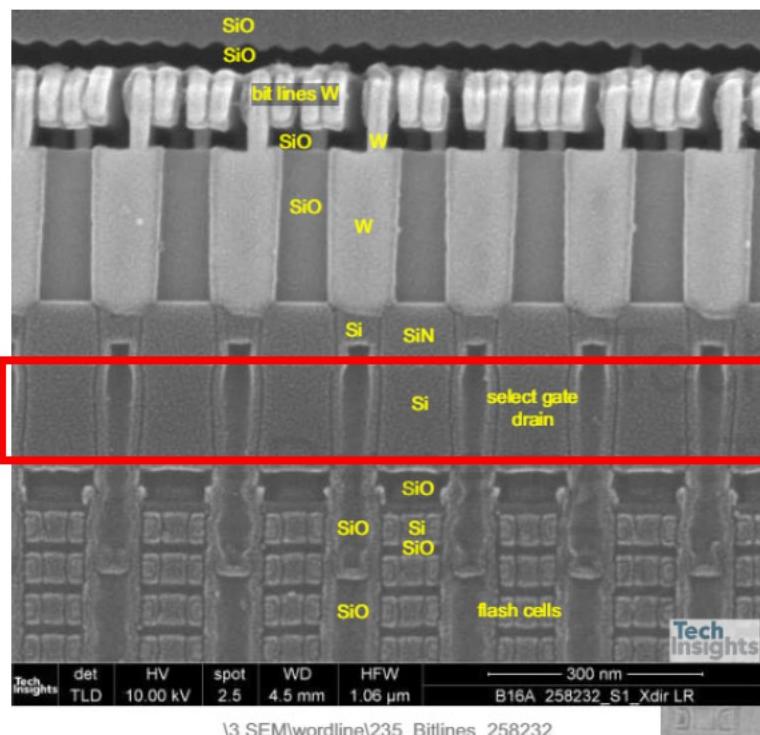
Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018

	 <p>bit line select gate drain 4.41 μm 74 stacked cells select gate source source contact plane WSi</p> <table border="1"> <tr> <td>Tech Insights</td><td>det</td><td>HV</td><td>spot</td><td>WD</td><td>HFW</td><td>2 μm</td></tr> <tr> <td>TLD</td><td>5.00 kV</td><td>2.0</td><td>4.6 mm</td><td>7.06 μm</td><td></td><td>B16A 258232_S2_Ydir LR</td></tr> </table> <p>\3 SEM\bitline\307_Central_Structure_258232</p>	Tech Insights	det	HV	spot	WD	HFW	2 μm	TLD	5.00 kV	2.0	4.6 mm	7.06 μm		B16A 258232_S2_Ydir LR	 <p>M4 bit lines drain select cell stack upper half center divide/tube landing cell stack lower half source select source contact plane 2.1 μm 2.1 μm</p> <table border="1"> <tr> <td>Tech Insights</td><td>det</td><td>HV</td><td>spot</td><td>WD</td><td>HFW</td><td>2 μm</td></tr> <tr> <td>TLD</td><td>10.00 kV</td><td>2.5</td><td>4.5 mm</td><td>6.68 μm</td><td></td><td>B16A 258232_S1_Xdir LR</td></tr> </table> <p>\3 SEM\wordline\222_Array_258232</p>	Tech Insights	det	HV	spot	WD	HFW	2 μm	TLD	10.00 kV	2.5	4.5 mm	6.68 μm		B16A 258232_S1_Xdir LR
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a plurality of horizontal select lines;	The 3D NAND Flash array has a plurality of wordlines, which are horizontal select lines.																													

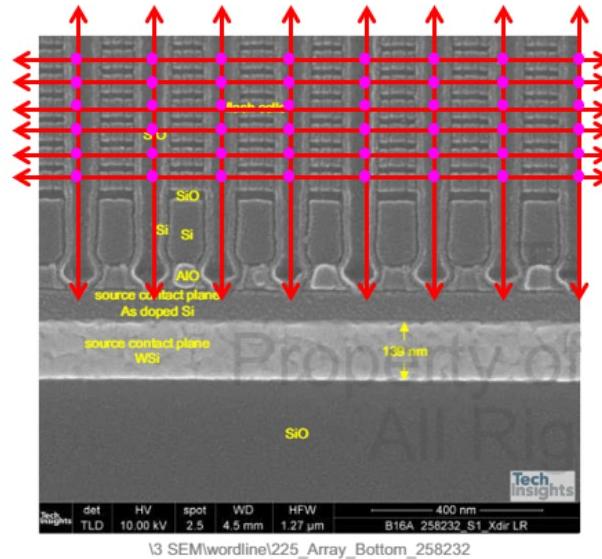
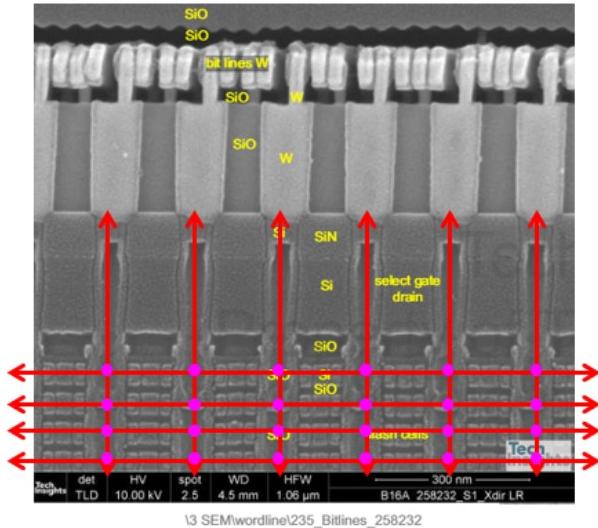


	Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018
a plurality of vertical select lines;	<p>The 3D NAND Flash array has a plurality of vertical select lines.</p>  
a plurality of memory cells, each memory cell adjacent to a horizontal select line and adjacent to a vertical select line; and	<p>Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018</p> <p>The 3D NAND Flash array has a plurality of floating gate memory cells, each memory cell adjacent to a horizontal select line and adjacent to a vertical select line.</p>



<p>at least one switching element disposed on top of at least one of the plurality of vertical select lines;</p>	<p>The 3D NAND Flash array has at least one switching element (select gate drain) disposed on top of at least one of the plurality of vertical select lines.</p>  <p>Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018</p>
<p>wherein the plurality of memory cells are arranged to form planes of horizontal select lines and planes of vertical select lines</p>	<p>The 3D NAND Flash array has the plurality of memory cells arranged to form planes of horizontal select lines and planes of vertical select lines orthogonal to each other.</p>

orthogonal to each other.



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